

Features

- Floating high-side driver in bootstrap operation to 600V
- Drives two N-channel MOSFETs or IGBTs in a half-bridge configuration
- 1.4A source / 1.8A sink output current capability
- Outputs tolerant to negative transients
- Programmable dead time to protect MOSFETs
- Wide low-side gate driver supply voltage: 10V to 20V
- Wide logic supply voltage offset voltage: -5V to 5V
- Logic input (IN and SD*) 3.3V capability
- Schmitt triggered logic inouts with internal pull down
- Undervoltage lockout for high and low side drivers
- Extended temperature range:-40°C to +125°C

Applications

- DC-DC Converters
- AC-DC Inverters
- Motor Controls
- Class D Power Amplifiers

TF21844M

Half-Bridge Gate Driver

Description

The TF21844M is a high voltage, high speed gate driver capable of driving N-channel MOSFETs and IGBTs in a half bridge configuration. TF Semiconductors's high voltage process enables the TF21844M's high side to switch to 600V in a bootstrap operation.

The TF21844M logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices. The driver outputs feature high pulse current buffers designed for minimum driver cross conduction. Programmable dead time, by an external resistor, provides more system level flexibility.

The TF21844M is offered in PDIP-14 and SOIC-14(N) packages. It operates over an extended -40 °C to +125 °C temperature



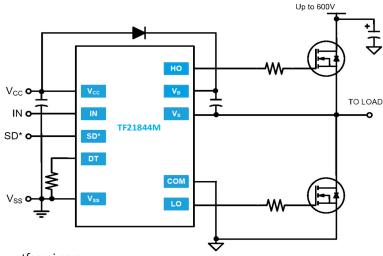


Ordering Information

Year Year Week Week

PART NUMBER	PACKAGE	PACK / Qty	MARK				
TF21844M-TUU	COIC 14(NI)	Tube / 50	TF21844M				
TF21844M-TUH	SOIC-14(N)	T&R / 2500	Lot ID				
TF21844M-3BS	PDIP-14	Tube / 25	TF21844M Lot ID				

Typical Application



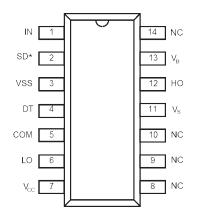
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Half-Bridge Gate Driver

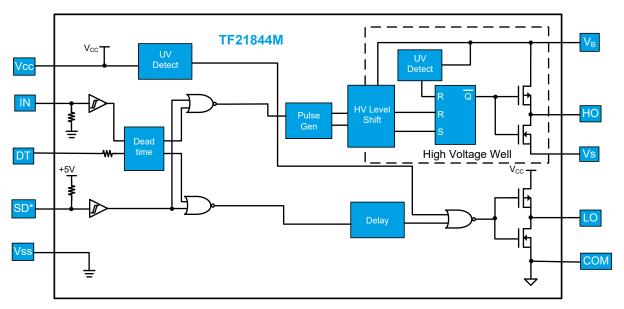


Top View: PDIP-14, SOIC-14 **TF21844M**

Pin Descriptions

PIN NAME	PIN DESCRIPTION
IN	Logic input for high-side and low-side gate driver outputs (HO and LO), in phase with HO (referenced to VSS).
SD*	Logic input for shutdown (referenced to VSS), enabled low.
V _{ss}	Logic ground
DT	Programmable deadtime lead, referenced to VSS.
COM	Low-side return
LO	Low-side gate drive output
V _{cc}	Low-side and logic fixed supply
V _B	High-side floating supply
НО	High-side gate drive output
V _s	High-side floating supply return

Functional Block Diagram



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Half-Bridge Gate Driver

Absolute Maximum Ratings (NOTE1)

$\rm V_B$ - High side floating supply voltage0.3V to +624V $\rm V_S$ - High side floating supply offset voltage $\rm V_B$ -24V to $\rm V_B$ +0.3V $\rm V_{HO}$ - High side floating output voltage $\rm V_S$ -0.3V to $\rm V_B$ +0.3V dV_S /dt - Offset supply voltage transient50 V/ns $\rm V_{DT}$ - Programmable dead time pin voltage $\rm V_{SS}$ -0.3V to $\rm V_{CC}$ +0.3V
$\rm V_{cc}$ - Logic and Low side fixed supply voltage0.3V to +24V $\rm V_{LO}$ - Low side output voltage0.3V to $\rm V_{cc}$ +0.3V $\rm V_{ss}$ - Logic supply offset voltage $\rm V_{cc}$ -24V to $\rm V_{cc}$ +0.3V $\rm V_{IN}$ - Logic input voltage (IN and SD*) $\rm V_{ss}$ -0.3V to $\rm V_{cc}$ +0.3V

NOTE1 Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

P_D - Package power dissipation at $T_A \le 25$ °C SOIC-14PDIP-14	
SOIC-14 Thermal Resistance (NOTE2)	
$ heta_{ extsf{IA}}$	120 °C/W
PDIP-14 Thermal Resistance (NOTE2)	
$ heta_{JA}$	75 °C/W
T _J - Junction operating temperature	+150 °C
T _L - Lead temperature (soldering, 10s)	+300 °C
T _{stg} - Storage temperature range	55 °C to +150 °C

NOTE2 When mounted on a standard JEDEC 2-layer FR-4 board.

Recommended Operating Conditions

Symbol	Parameter	MIN	MAX	Unit
V _B	High side floating supply absolute voltage	V _s + 10	V _s + 20	V
V _s	High side floating supply offset voltage	NOTE3	600	V
V _{HO}	High side floating output voltage	V _s	V _B	V
V _{cc}	Logic and Low side fixed supply voltage	10	20	V
V _{LO}	Low side output voltage	0	V _{cc}	V
V _{IN}	Logic input voltage (IN & SD*)	V _{ss}	5	V
V _{DT}	Programmable deadtime pin voltage	V _{ss}	V _{cc}	V
V _{ss}	Logic ground	-5	+5	V
T _A	Ambient temperature	-40	125	°C

NOTE3 Logic operational for VS of -5V to 600V.



DC Electrical Characteristics (NOTE4)

 $\rm V_{\rm CC} = \rm V_{\rm BS} = 15V, \rm V_{\rm SS} = COM,$ and $\rm T_{\rm A} = 25~^{\circ}C$, unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
V _{IH}	Logic "1" input voltage for HO & logic "0" for LO		2.5			
V _{IL}	Logic "0" input voltage for HO & logic "1" for LO	$V_{CC} = 10 \text{ V to } 20 \text{ V}$			0.8	V
$V_{SD,TH+}$	SD* input poitive going threshold	NOTE5	2.5			_ v
V _{SD, TH-}	SD* input negative going threshold				0.8	
V _{OH}	High level output voltage, V _{BIAS} - V _O	I ₀ = 0A			1.4	
V _{OL}	Low level output voltage, V _o	I _o = 20mA			0.2	
I _{LK}	Offset supply leakage current	VB = VS = 600V			50	
I _{BSO}	Quiescent V _{BS} supply current	V _{IN} = 0V or 5V	20	60	150	T μA
I _{ccq}	Quiescent V _{cc} supply current	V _{IN} = 0V or 5V	0.4	1.0	1.8	mA
I _{IN+}	Logic "1" input bias current	IN= 5V, SD* = 0V		25	60	_
I _{IN-}	Logic "0" input bias current	IN= 0V, SD* = 5V			1.0	μΑ
V_{BSUV+}	V _{BS} supply under-voltage positive going threshold		8	8.9	9.8	
V_{BSUV}	V _{BS} supply under-voltage negative going threshold		7.4	8.2	9	V
$V_{\text{CCUV+}}$	V _{cc} supply under-voltage positive going threshold		8	8.9	9.8	
V _{CCUV} -	V _{cc} supply under-voltage negative going threshold		7.4	8.2	9.0	
I _{O+}	Output high short circuit pulsed current	$V_{o} = 0V, PW \le 10 \ \mu s$	1.4	1.9		
I _{O-}	Output low short circuit pulsed current	$V_0 = 15V, PW \le 10 \mu s$	1.7	2.3		A

NOTE4 The V_{M} V_{TH} I_{M} parameters are referenced to V_{SS} and are applicable to the two logic input pins: IN and SD*. The V_{0} and I_{0} parameters are referenced to COM and are applicable to the respective output pins: HO and LO.

NOTE5 For optimal operation, it is highly recommended that the input pulse (to IN and SD*) should have an amplitude of 2.5V minimum with a pulse width of 2 x tdt (deadtime) minimum.



Half-Bridge Gate Driver

AC Electrical Characteristics

 $V_{BIAS}(V_{CC},V_{BS})=15V,V_{SS}=COM,C_{L}=1000~pF,$ and $T_{A}=25~^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
t _{on}	Turn-on propagation delay	$V_s = 0V$		680	900	
t _{OFF}	Turn-off propagation delay	$V_{s} = 0 \text{ V or } 600 \text{ V}$		270	400	
t _{sd}	Shut-down propagation delay			180	270	
t _{DM ON}	Delay matching, HS & LS turn-on				90	ns
t _{DM OFF}	Delay matching, HS & LS turn-off				40	
t _r	Turn-on rise time	$V_s = 0V$		40	60	
t _f	Turn-off fall time			20	35	
		$R_{DT} = 0\Omega$	280	400	520	ns
t _{DT}	Deadtime: t _{DT LO-HO} & t _{DT HO-LO}	$R_{DT} = 200 k\Omega$	4	5	6	μs
		$R_{DT} = 0\Omega$		0	50	
t _{MDT}	Deadtime matching = $t_{DT LO-HO} - t_{DT HO-LO}$	$R_{DT} = 200 k\Omega$		0	600	ns

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Timing Waveforms

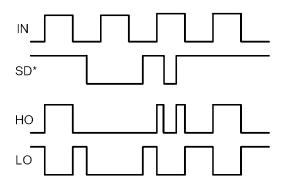


Figure 1. Input / Output Timing Diagram

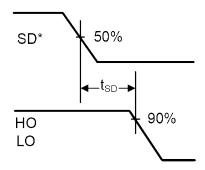
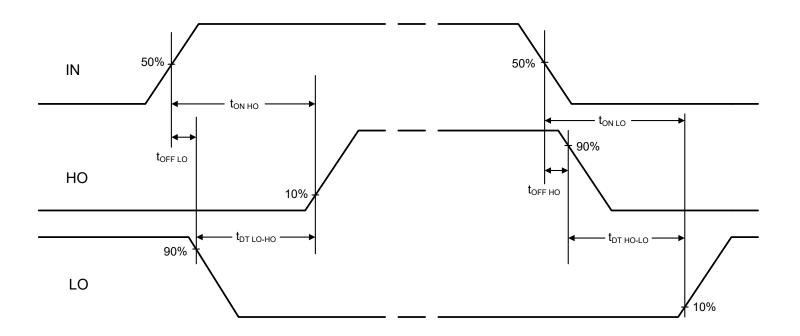


Figure 2. Shutdown Waveform Definitions



Deadtime $t_{DT LO-HO} = t_{ON HO} - t_{OFF LO}$ $t_{DT HO-LO} = t_{ON LO} - t_{OFF HO}$

Deadtime matching $t_{\text{MDT}} = t_{\text{DT LO-HO}}$ - $t_{\text{DT HO-LO}}$

Delay matching $t_{\text{DM OFF}} = t_{\text{OFF LO}} - t_{\text{OFF HO}}$

 $t_{\rm DM~ON}$ = $t_{\rm ON~LO}$ - $t_{\rm ON~HO}$

Figure 3. Switching Time Waveform Definitions



Application Information

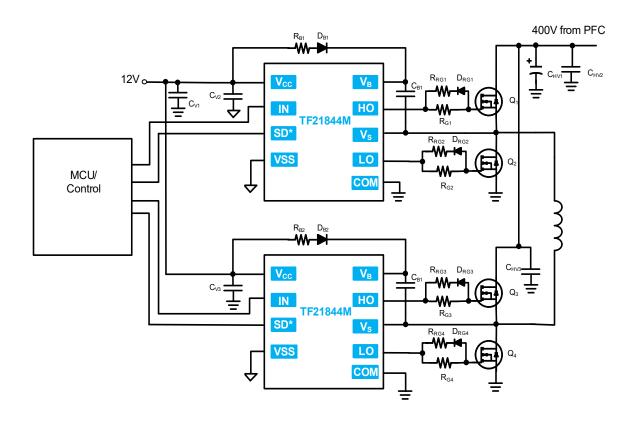


Figure 4. Primary side of Full Bridge converter using TF21844M

- RRG1, RRG2, RRG3, and RRG4 values are typically between 0Ω and 10Ω , exact value decided by MOSFET junction capacitance and drive current of gate driver; 10Ω is used in this example.
- It is **highly recommended** that the input pulse (to IN and SD*) should have an amplitude of 2.5V minimum (for VDD=15V) with a minimum pulse width of 2 x tdt (deadtime).
- **RG1**, RG2, RG3, and RG4 values are typically between 10Ω and 100Ω , exact value decided by MOSFET junction capacitance and drive current of gate driver; 50Ω is used in this example.
- RB1 and RB2 value is typically between 3Ω and 20Ω , exact value depending on bootstrap capacitor value and amount of current limiting required for bootstrap capacitor charging; 10Ω is used in this example. Also DB1 and DB2 should be an ultra fast diode of 1A rating minimum and voltage rating greater than system operating voltage.

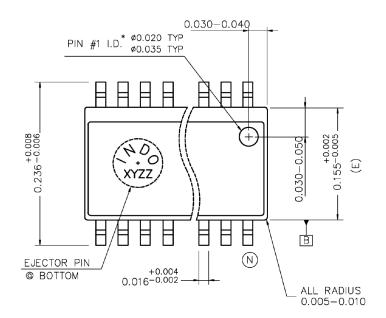
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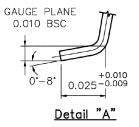
Package Dimensions (SOIC-14)

Please contact support@tfsemi.com for package availability.

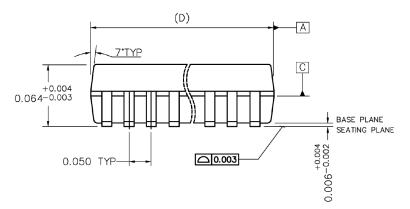


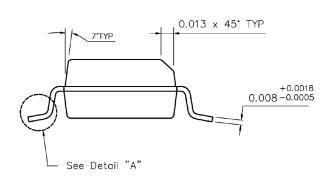
ALL DIMENSIONS ARE IN INCHES UNLESS OTHERWISE NOTED

- 1. "D" & "E" ARE REFERENCE DATUMS AND DO NOT INCLUDE MOLD FLASH OR PROTRUSION. MOLD FLASH OR PROTRUSION SHALL NOT EXCEED 6 MILS PER SIDE.
- 2. "N" IS THE NUMBER OF TERMINAL POSITIONS.
- 3. FORMED LEADS SHALL BE PLANAR WITH RESPECT TO ONE ANOTHER WITHIN 3 MIL: (SEATING PLANE) OUTGOING ASSEMBLY & 4 MILS AFTER TEST.
- 4. THE BOTTOM PACKAGE LEAD SIDE MAY BE BIGGER THAN THE TOP PACKAGE LEAD SIDE BY 4 MILS (2 MILS PER SIDE). BOTTOM PACKAGE DIMENSION SHALL FOLLOW DIMENSION STATED IN THIS DRAWING.
- 5. THE BOTTOM EJECTOR PIN CONTAINS COUNTRY OF ORIGIN "INDO" AND MOLD ID. (REFER TO TABLE FOR OPTION).
- 6. THIS DRAWING CONFORMS TO JEDEC REF. MS-012 REV. E



		D VARIATION		MGP MOLD				
	N	_ b \	/ARIA II	STANDARD MATE		RIX		
	IN	MIN	ном	мах	PIN 1 I.D.	EJECT PIN	PIN 1 I.D.	EJECT PIN
	08	0.189	0.193	0.196	N/A		YES	YES
	14	0.337	0.339	0.344	YES	NO	YES	YES
◬	16	0.386	0.390	0.393	N	/A	YES	YES



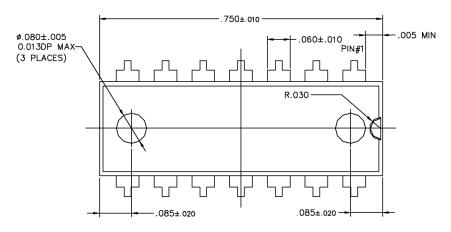


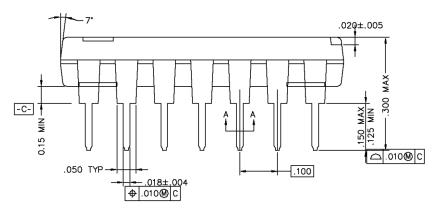


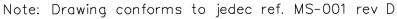
Package Dimensions (PDIP-14)

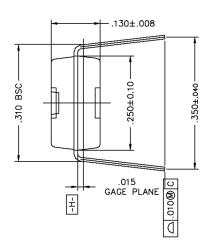
Please contact support@tfsemi.com for package availability.

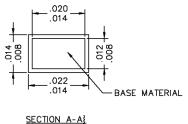
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Rev.	Change	Owner	Date	
1.0	First release, final datasheet	Keith Spaulding	9/22/2020	
1.1	Application notes update	Raj Selvaraj	06/22/2021	

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